

MOS INTEGRATED CIRCUIT

μ PD464318L, 464336L

4M-BIT Bi-CMOS SYNCHRONOUS FAST STATIC RAM 256K-WORD BY 18-BIT / 128K-WORD BY 36-BIT HSTL INTERFACE

Description

The μ PD464318L is a 262,144 words by 18 bits, and the μ PD464336L is a 131,072 words by 36 bits synchronous static RAM fabricated with advanced Bi-CMOS technology using N-channel memory cell.

This technology and unique peripheral circuits make the μ PD464318L and μ PD464336L a high-speed device. The μ PD464318L and μ PD464336L are suitable for applications which require high-speed, low voltage, high-density memory and wide bit configuration, such as cache and buffer memory.

These are packaged in a 119-pin plastic BGA (Ball Grid Array).

Features

- Fully synchronous operation
- Fast clock access time : 2.6 ns / 200 MHz, 3.0 ns / 167 MHz, 3.5 ns / 154 MHz
- Single Differential Single clock, Registered Input / Registered Output
- Asynchronous output enable control : /G
- Byte write control : /SBa (DQa1-9), /SBb (DQb1-9), /SBc (DQc1-9), /SBd (DQd1-9)
- Common I/O using three-state outputs
- Internally self-timed write cycle
- Late write with 1 dead cycle between Read-Write
- User-configurable outputs :
Controlled impedance outputs or push-pull outputs
- Boundary scan (JTAG) IEEE 1149.1 compatible
- 3.3 V (Chip) / 1.5V (I/O) supply

Ordering Information

Part number	Access time	Clock frequency	Package
μ PD464318LS1-A5	2.6 ns	200 MHz	119-pin plastic BGA
μ PD464318LS1-A6	3.0 ns	167 MHz	
μ PD464318LS1-A65	3.5 ns	154 MHz	
μ PD464336LS1-A5	2.6 ns	200 MHz	
μ PD464336LS1-A6	3.0 ns	167 MHz	
μ PD464336LS1-A65	3.5 ns	154 MHz	

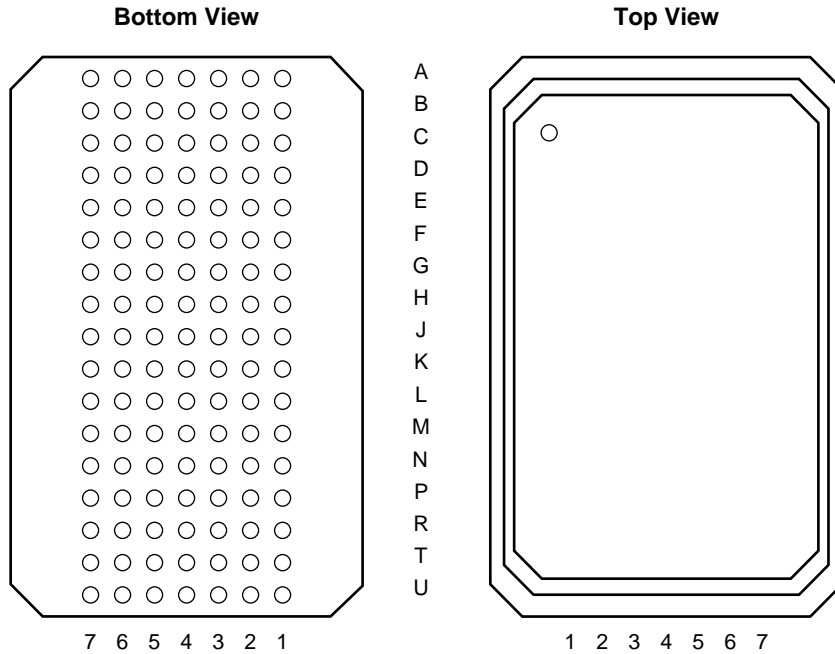
The information in this document is subject to change without notice.

Pin Configurations

/xxx indicates active low signal.

119-pin Plastic BGA (256K Words by 18 Bits Pin Assignment)

[μPD464318LS1]



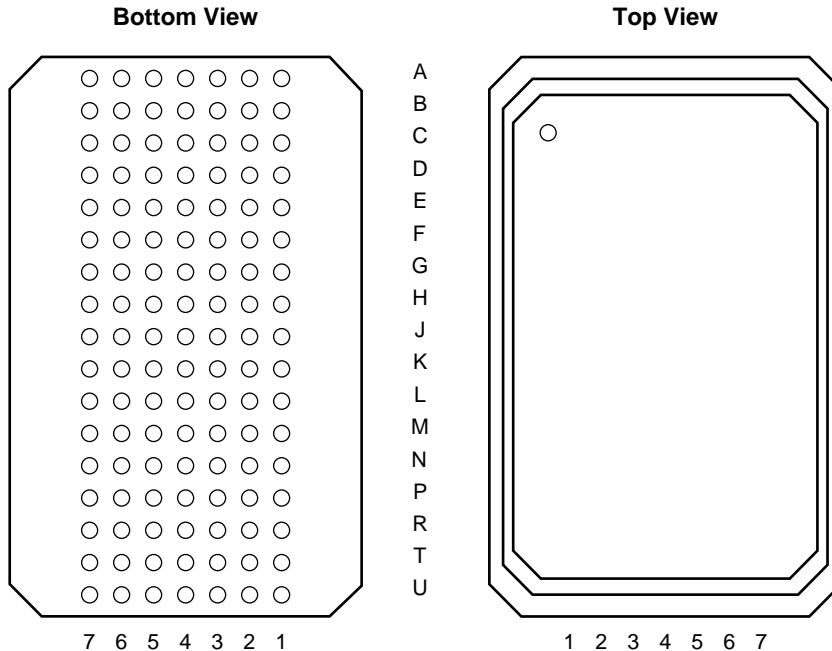
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	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.
A	A7	VDDQ	A6	SA2	A5	SA6	A4	NC	A3	SA9	A2	SA12	A1	VDDQ
B	B7	NC	B6	NC	B5	SA16	B4	NC	B3	SA17	B2	NC	B1	NC
C	C7	NC	C6	SA3	C5	SA7	C4	VDD	C3	SA10	C2	SA13	C1	NC
D	D7	NC	D6	DQa9	D5	VSS	D4	ZQ	D3	VSS	D2	NC	D1	DQb1
E	E7	DQa8	E6	NC	E5	VSS	E4	/SS	E3	VSS	E2	DQb2	E1	NC
F	F7	VDDQ	F6	DQa7	F5	VSS	F4	/G	F3	VSS	F2	NC	F1	VDDQ
G	G7	DQa6	G6	NC	G5	VSS	G4	NC	G3	/SBb	G2	DQb3	G1	NC
H	H7	NC	H6	DQa5	H5	VSS	H4	NC	H3	VSS	H2	NC	H1	DQb4
J	J7	VDDQ	J6	VDD	J5	VREF	J4	VDD	J3	VREF	J2	VDD	J1	VDDQ
K	K7	DQa4	K6	NC	K5	VSS	K4	K	K3	VSS	K2	DQb5	K1	NC
L	L7	NC	L6	DQa3	L5	/SBa	L4	/K	L3	VSS	L2	NC	L1	DQb6
M	M7	VDDQ	M6	NC	M5	VSS	M4	/SW	M3	VSS	M2	DQb7	M1	VDDQ
N	N7	NC	N6	DQa2	N5	VSS	N4	SA1	N3	VSS	N2	NC	N1	DQb8
P	P7	DQa1	P6	NC	P5	VSS	P4	SA0	P3	VSS	P2	DQb9	P1	NC
R	R7	NC	R6	SA4	R5	VDD	R4	VDD	R3	VSS	R2	SA14	R1	NC
T	T7	NC	T6	SA5	T5	SA8	T4	NC	T3	SA11	T2	SA15	T1	NC
U	U7	VDDQ	U6	NC	U5	TDO	U4	TCK	U3	TDI	U2	TMS	U1	VDDQ

Pin Name and Functions

Pin name	Description	Function
VDD	Core Power Supply	Supplies power for RAM core
VSS	Ground	
VDDQ	Output Power Supply	Supplies power for output buffers
VREF	Input Reference	
K, /K	Main Clock Input	
SA0 to SA17	Synchronous Address Input	
DQa1 to DQb9	Synchronous Data Input / Output	
/SS	Synchronous Chip Select	Logically selects SRAM
/SW	Synchronous Byte Write Enable	
/SBa	Synchronous Byte "a" Write Enable	Write DQa1 to DQa9
/SBb	Synchronous Byte "b" Write Enable	Write DQb1 to DQb9
/G	Asynchronous Output Enable	Asynchronous input
ZQ	Output Impedance Control	
NC	No Connection	
TMS	Test Mode Select (JTAG)	
TDI	Test Data Input (JTAG)	
TCK	Test Clock Input (JTAG)	
TDO	Test Data Output (JTAG)	

119-pin plastic BGA (128K Words by 36 Bits Pin Assignment)

[μPD464336LS1]

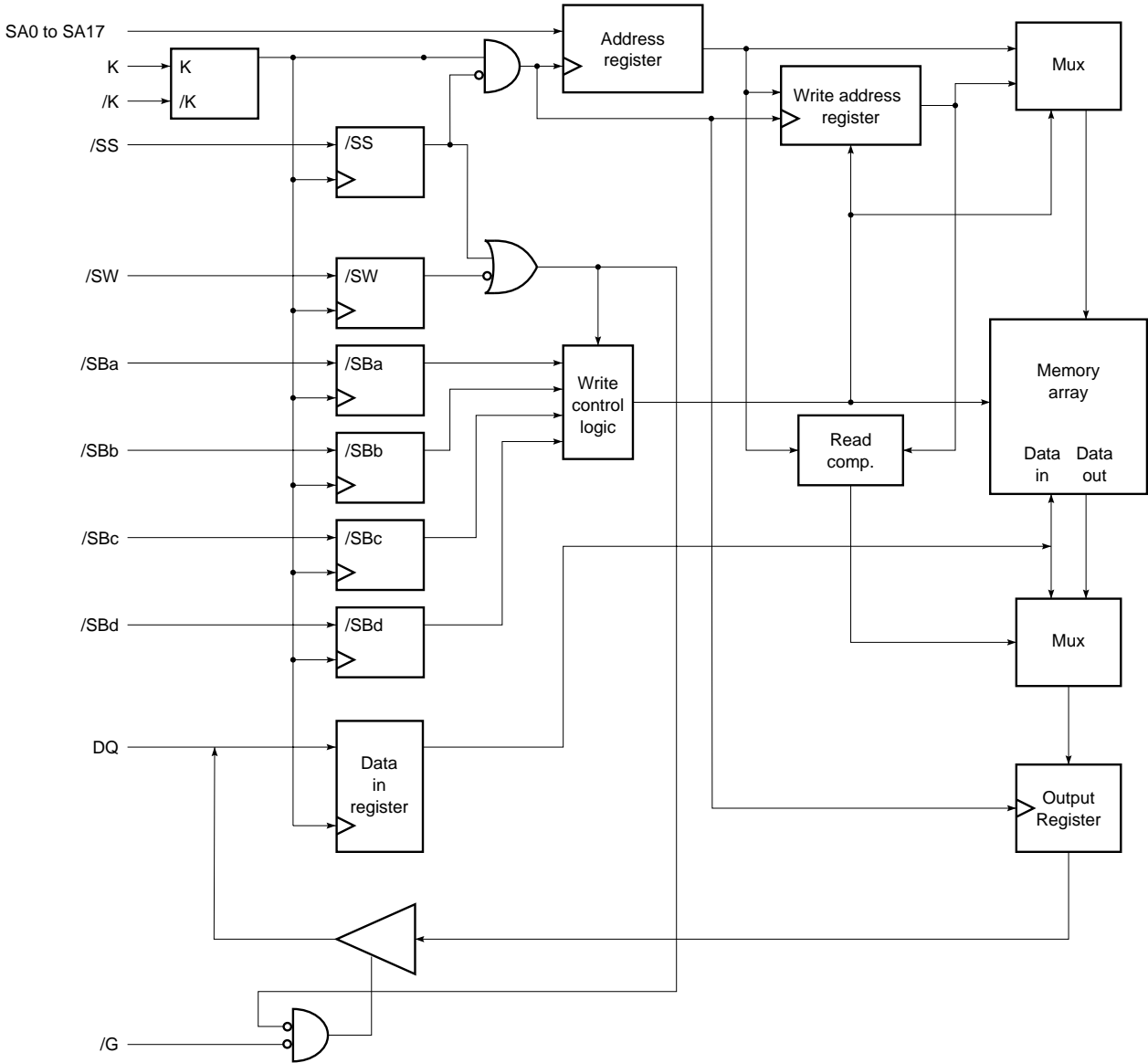


	7		6		5		4		3		2		1	
	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.	Pin No.	Func.
A	A7	VDDQ	A6	SA2	A5	SA5	A4	NC	A3	SA9	A2	SA12	A1	VDDQ
B	B7	NC	B6	NC	B5	SA15	B4	NC	B3	SA16	B2	NC	B1	NC
C	C7	NC	C6	SA3	C5	SA6	C4	VDD	C3	SA10	C2	SA13	C1	NC
D	D7	DQb8	D6	DQb9	D5	VSS	D4	ZQ	D3	VSS	D2	DQc9	D1	DQc8
E	E7	DQb6	E6	DQb7	E5	VSS	E4	/SS	E3	VSS	E2	DQc7	E1	DQc6
F	F7	VDDQ	F6	DQb5	F5	VSS	F4	/G	F3	VSS	F2	DQc5	F1	VDDQ
G	G7	DQb3	G6	DQb4	G5	/SBb	G4	NC	G3	/SBc	G2	DQc4	G1	DQc3
H	H7	DQb1	H6	DQb2	H5	VSS	H4	NC	H3	VSS	H2	DQc2	H1	DQc1
J	J7	VDDQ	J6	VDD	J5	VREF	J4	VDD	J3	VREF	J2	VDD	J1	VDDQ
K	K7	DQa1	K6	DQa2	K5	VSS	K4	K	K3	VSS	K2	DQd2	K1	DQd1
L	L7	DQa3	L6	DQa4	L5	/SBa	L4	/K	L3	/SBd	L2	DQd4	L1	DQd3
M	M7	VDDQ	M6	DQa5	M5	VSS	M4	/SW	M3	VSS	M2	DQd5	M1	VDDQ
N	N7	DQa6	N6	DQa7	N5	VSS	N4	SA1	N3	VSS	N2	DQd7	N1	DQd6
P	P7	DQa8	P6	DQa9	P5	VSS	P4	SA0	P3	VSS	P2	DQd9	P1	DQd8
R	R7	NC	R6	SA4	R5	VDD	R4	VDD	R3	VSS	R2	SA14	R1	NC
T	T7	NC	T6	NC	T5	SA7	T4	SA8	T3	SA11	T2	NC	T1	NC
U	U7	VDDQ	U6	NC	U5	TDO	U4	TCK	U3	TDI	U2	TMS	U1	VDDQ

Pin Name and Functions

Pin name	Description	Function
VDD	Core Power Supply	Supplies power for RAM core
VSS	Ground	
VDDQ	Output Power Supply	Supplies power for output buffers
VREF	Input Reference	
K, /K	Main Clock	
SA0 to SA16	Synchronous Address Input	
DQa1 to DQd9	Synchronous Data Input / Output	
/SS	Synchronous Chip Select	Logically selects SRAM
/SW	Synchronous Byte Write Enable	
/SBa	Synchronous Byte "a" Write Enable	Write DQa1 to DQa9
/SBb	Synchronous Byte "b" Write Enable	Write DQb1 to DQb9
/SBc	Synchronous Byte "c" Write Enable	Write DQc1 to DQc9
/SBd	Synchronous Byte "d" Write Enable	Write DQd1 to DQd9
/G	Asynchronous Output Enable	Asynchronous input
ZQ	Output Impedance Control	
NC	No Connection	
TMS	Test Mode Select (JTAG)	
TDI	Test Data Input (JTAG)	
TCK	Test Clock Input (JTAG)	
TDO	Test Data Output (JTAG)	

★ Late Write Block Diagram



Synchronous Truth Table

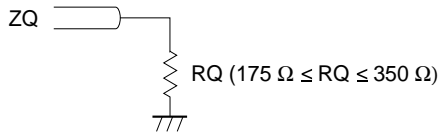
/SS	/SW	/SBa	/SBb	/SBc	/SBd	Mode	DQa1-9	DQb1-9	DQc1-9	DQd1-9	Power
H	×	×	×	×	×	Not selected	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Active
L	H	×	×	×	×	Read	Dout	Dout	Dout	Dout	Active
L	L	L	L	L	L	Write	Din	Din	Din	Din	Active
L	L	L	H	H	H	Write	Din	Hi-Z	Hi-Z	Hi-Z	Active
L	L	H	L	L	L	Write	Hi-Z	Din	Din	Din	Active

Remark × : Don't care

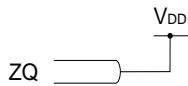
Mode Select (Output Buffer)

ZQ	Mode	Notes
IZQ × RQ	Controlled impedance push-pull output buffer mode	1
VDD	Push-Pull output buffer mode	2

Notes 1. See figure.



2. See figure.



Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit	Note
Supply voltage	V _{DD}		-0.5		+4	V	1
Output supply voltage	V _{DDQ}		-0.5		+4	V	1
Input voltage	V _{IN}		-0.5		V _{DD} + 0.3	V	1
Input / Output voltage	V _{I/O}		-0.5		V _{DDQ} + 0.3	V	1
Operating temperature	T _j		20		110	°C	2
Storage temperature	T _{stg}		-55		+125	°C	

Notes 1. -0.5 V MIN. (Pulse width 10% T_{cyc})

2. T_j = Junction temperature

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended DC Operating Conditions (T_j = 20 to 110 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Core supply voltage	V _{DD}		3.15	3.3	3.45	V
Output buffer supply voltage	V _{DDQ}		1.4	1.5	1.6	V
Input reference voltage	V _{REF}		0.6	0.95	1.3	V
Low level input voltage	V _{IL}		-0.3 ^{Note}		V _{REF} -0.1	V
High level input voltage	V _{IH}		V _{REF} +0.1		V _{DDQ} +0.3	V

Note -0.5 V MIN. (Pulse width 10% T_{cyc})

Recommended AC Operating Conditions (T_j = 20 to 110 °C) ^{Note}

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input reference voltage	V _{REF} (RMS)		-5%		+5%	V
Low level input voltage	V _{IL}		-0.3		V _{REF} -0.2	V
High level input voltage	V _{IH}		V _{REF} +0.2		V _{DDQ} +0.3	V

Note T_j = 20 to 110°C : μPD464318L-A6/ -A65, 464336L-A6/ -A65

T_j = 20 to 100°C : μPD464318L-A5, 464336L-A5

Capacitance (T_A = 25 °C, f = 1 MHz)

Parameter ^{Note}	Symbol	Test conditions	MAX.	Unit
Input capacitance	C _{IN}	V _{IN} = 0 V	5	pF
Input / Output capacitance	C _{I/O}	V _{I/O} = 0 V	7	pF
Clock pin (K, /K) input capacitance	C _{CLK}	V _{CLK} = 0 V	7	pF

Note These parameters are sampled and not 100% tested.

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

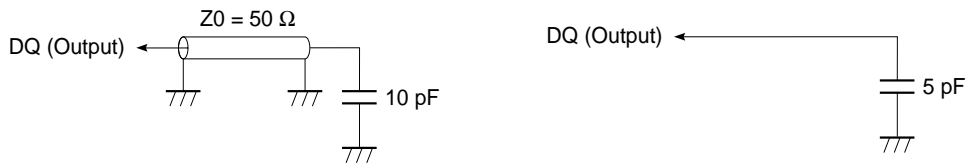
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input leakage current	I _{LI}	V _{IN} = 0 to V _{DD}	-5		+5	μA
DQ leakage current ^{Note}	I _{LO}	V _{I/O} = 0 to V _{DDQ}	-5		+5	μA
Operating supply current	I _{CC}	/SS = V _{IL} , I _{DQ} = 0 mA 200 MHz	μPD464318L		600	mA
			μPD464336L		700	

Note /SS = V_{IH} or /G = V_{IH}

Output Voltage on Controlled Impedance Push-Pull Output Buffer Mode (V_{ZQ} = I_{ZQ} × R_Q)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low level output voltage	V _{OL}	I _{OL} ≤ 10 μA, I _{OL} = 2.5V _{DDQ} / R _Q ± 10% V _{OL} = V _{DDQ} / 2 (175 Ω < R _Q < 350 Ω)	V _{SS}		0.1	V
High level output voltage	V _{OH}	I _{OH} ≤ 10 μA, I _{OH} = 2.5V _{DDQ} / R _Q ± 10% V _{OH} = V _{DDQ} / 2 (175 Ω < R _Q < 350 Ω)	V _{DDQ} -0.1		V _{DDQ}	V

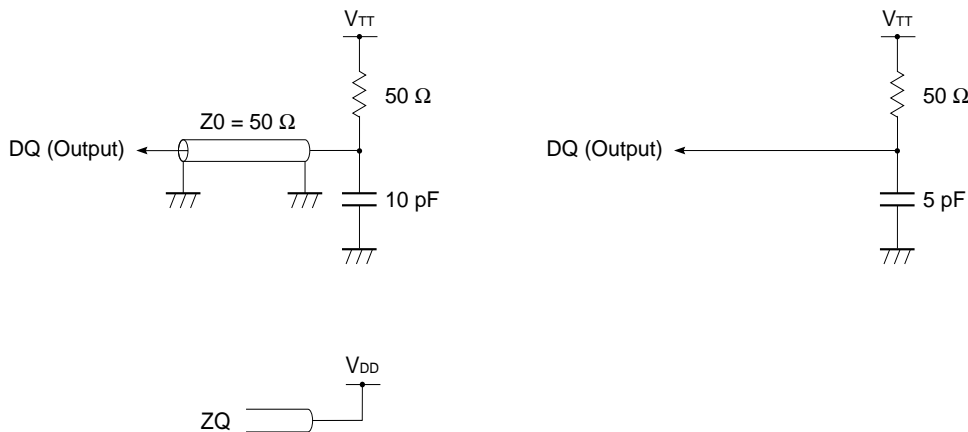
Remark See figure.



Output Voltage on Push-Pull Output Buffer Mode (V_{ZQ} = V_{DD})

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low level output voltage	V _{OL}	I _{OL} = +4 mA	-		0.3	V
High level output voltage	V _{OH}	I _{OH} = -4 mA	V _{DDQ} -0.3		-	V

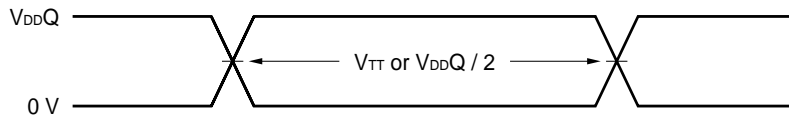
Remark See figure (V_{TT} = 0.75 V).



AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

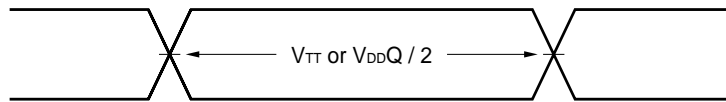
AC Characteristics Test Conditions

Input waveform (rise and fall time = 0.5 ns (20 to 80%))



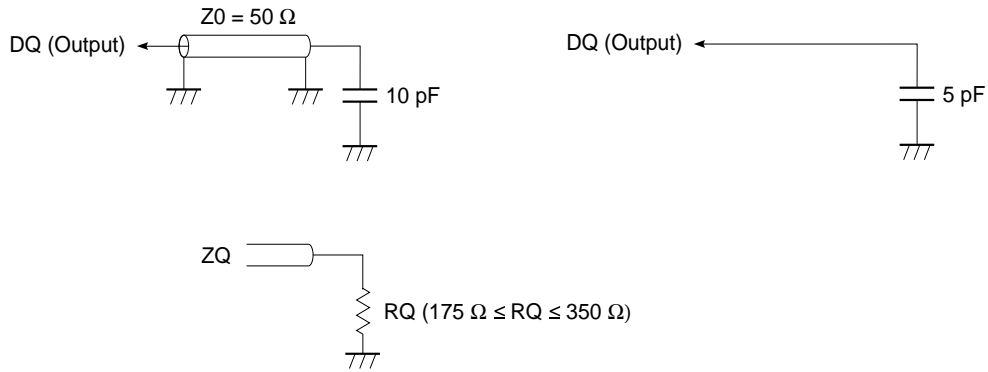
★ **Remark** Clock input differential voltage

Output waveform

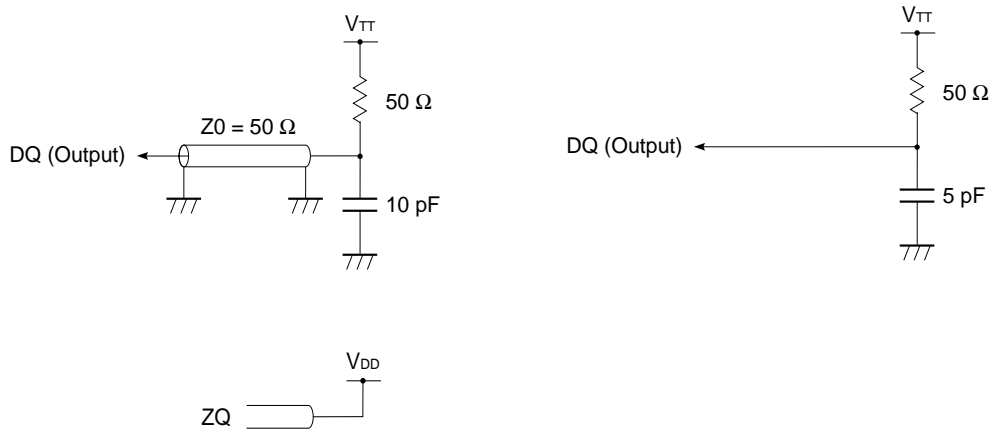


Output load

(1) Controlled impedance push-pull output buffer mode



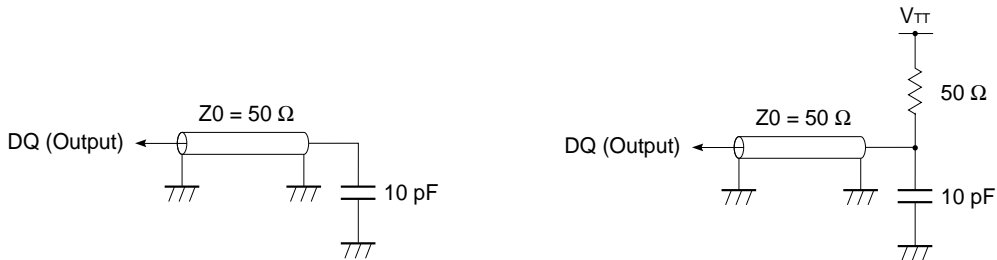
(2) Push-Pull output buffer mode ($V_{TT}=0.75 \text{ V}$)



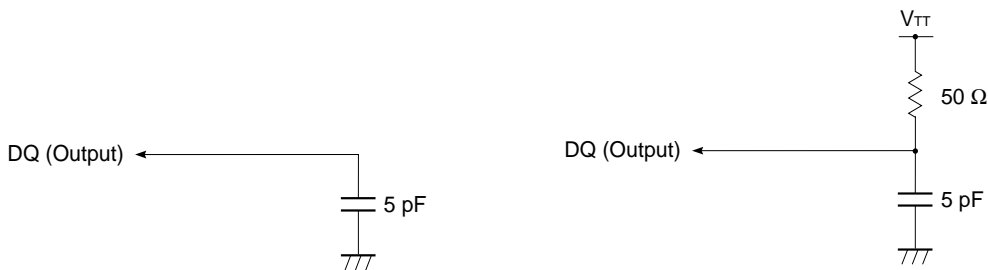
Single Differential Clock, Registered Input / Registered Output Mode

Parameter	Symbol	-A5 (200 MHz)		-A6 (167 MHz)		-A65 (154 MHz)		Unit	Notes	
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.			
Clock cycle time	TKHKH	5.0	–	6.0	–	6.5	–	ns		
Clock phase time	TKHKL / TKLKH	2.4	–	2.5	–	3.0	–	ns		
Setup times	Address	TAVKH	0.5	–	0.5	–	0.5	–	ns	
	Write data	TDVKH								
	Write enable	TWVKH								
	Chip select	TSVKH								
Hold times	Address	TKHAX	1.0	–	1.0	–	1.0	–	ns	
	Write data	TKHDX								
	Write enable	TKHWX								
	Chip select	TKHSX								
Clock access time	TKHQV	–	2.6	–	3.0	–	3.5	ns	1	
K high to Q change	TKHQX	1.0	–	1.0	–	1.0	–	ns	2	
/G low to Q valid	TGLQV	–	2.5	–	3.0	–	3.5	ns	1	
/G low to Q change	TGLQX	1.0	–	1.0	–	1.0	–	ns	2	
/G high to Q Hi-Z	TGHQZ	1.0	2.5	1.0	3.0	1.0	3.5	ns	2	
K high to Q Hi-Z (/SW)	TKHQZ	1.0	3.5	1.0	3.5	1.0	4.0	ns	2	
K high to Q Hi-Z (/SS)	TKHQZ2	1.0	3.5	1.0	3.5	1.0	4.0	ns	2	
K high to Q Lo-Z	TKHQX2	1.0	–	1.0	–	1.0	–	ns		
/G high Pulse width	TGHGL	5.0	–	6.0	–	6.5	–	ns	3	
/G high to K high	TGHKH	1.0	–	1.0	–	1.0	–	ns	3	
K high to /G low	TKHGL	2.5	–	2.5	–	2.5	–	ns	3	

Notes 1. See figure.

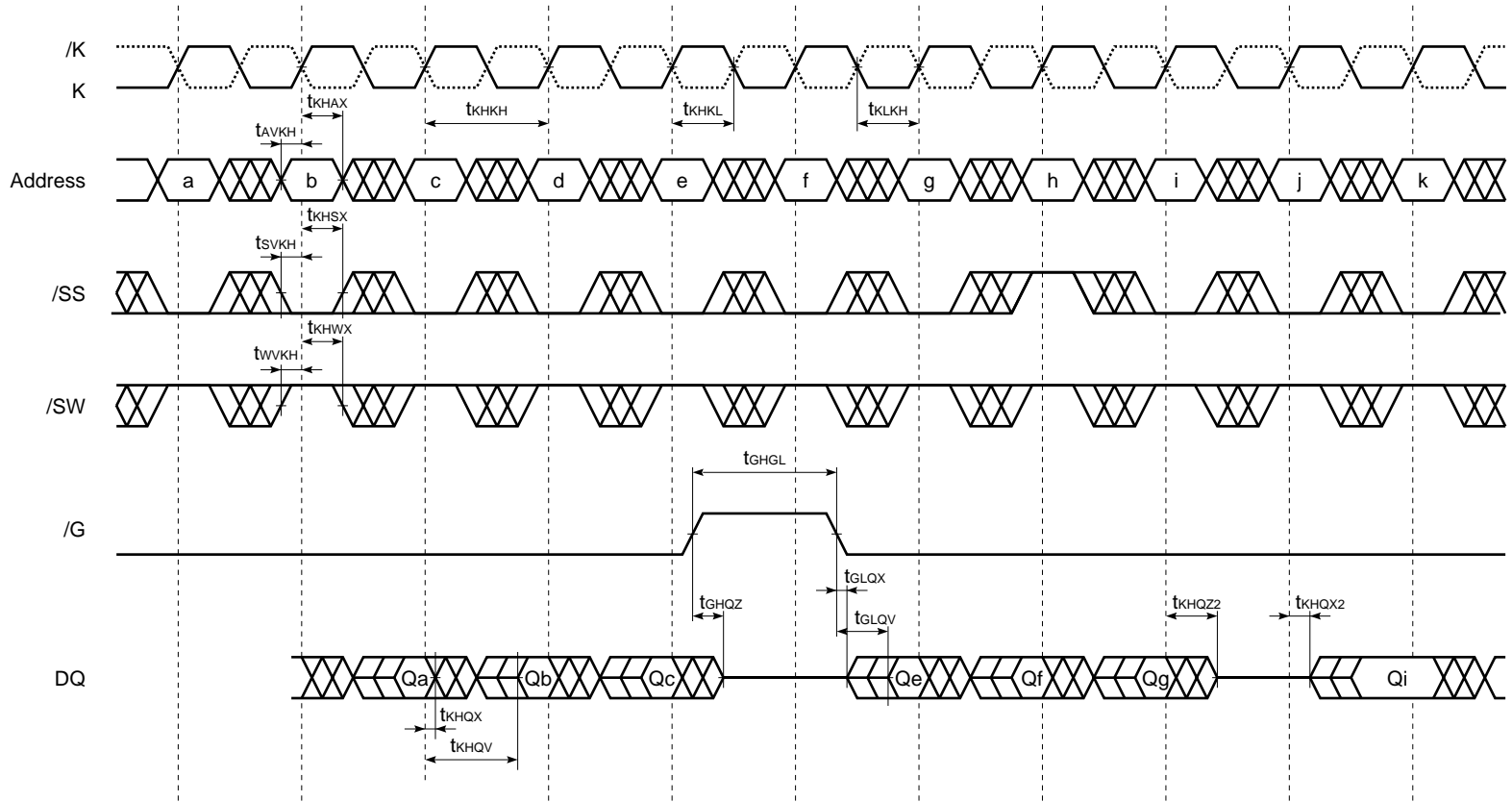


2. See figure.

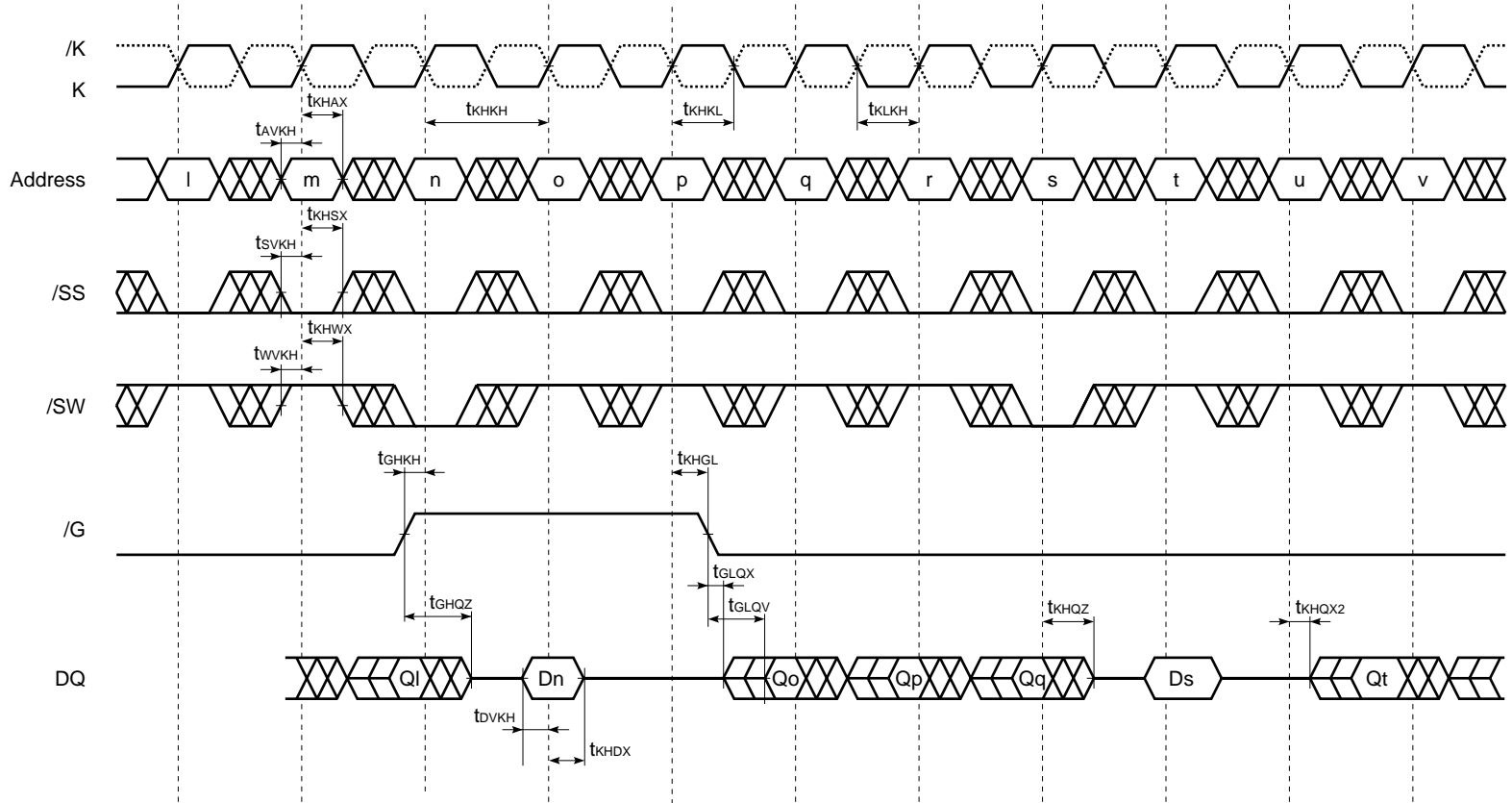


3. Controlled impedance push-pull output buffer mode only.

Single Differential Clock, Registered Input / Registered Output Mode (Read Operation)



Single Differential Clock, Registered Input / Registered Output Mode (Write Operation)



JTAG Specifications

The μPD464318L and μPD464336L support a limited set of JTAG functions as in IEEE standard 1149.1.

Test Access Port (TAP) Pins

Pin Name	Description	Pin Assignments
TCK	Test Clock Input	4 U
TMS	Test Mode Select	2 U
TDI	Test Data Input	3 U
TDO	Test Data Output	5 U

Remark The device does not have TRST (TAP reset). The TAP controller state is reset into TEST-LOGIC-RESET on the SRAM POWER-UP.

JTAG DC Characteristics (T_j = 20 to 110 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Notes
JTAG input high voltage	V _{IH}		2.2		V _{DD} +0.3	V	
JTAG input low voltage	V _{IL}		-0.3		+0.8	V	
JTAG output high voltage	V _{OH}		2.4		-	V	1
JTAG output low voltage	V _{OL}		-		0.4	V	2

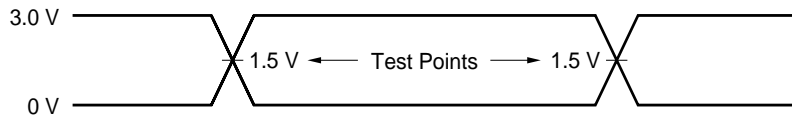
- Notes**
1. I_{OH} = -8 mA
 2. I_{OL} = 8 mA

JTAG AC Characteristics (T_j = 20 to 110 °C)

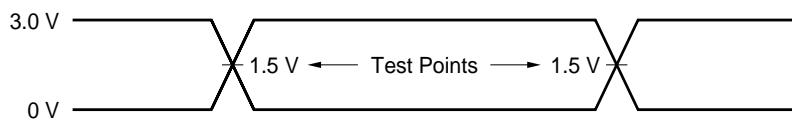
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Note
Clock Cycle Time (TCK)	t _{THTH}		100		-	ns	
Clock Phase Time (TCK)	t _{THTL} / t _{TLTH}		40		-	ns	
Setup Time (TMS / TDI)	t _{MVTH} / t _{DVTH}		10		-	ns	
Hold Time (TMS / TDI)	t _{THMX} / t _{THDX}		10		-	ns	
TCK Low to TDO Valid (TDO)	t _{TLQV}		-		20	ns	

JTAG AC Test Conditions ($T_j = 20$ to 110 °C)

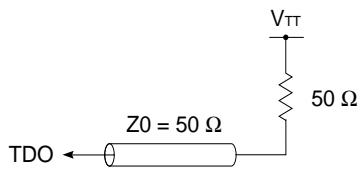
Input waveform (rise / fall time = 1 ns (20 to 50 %))



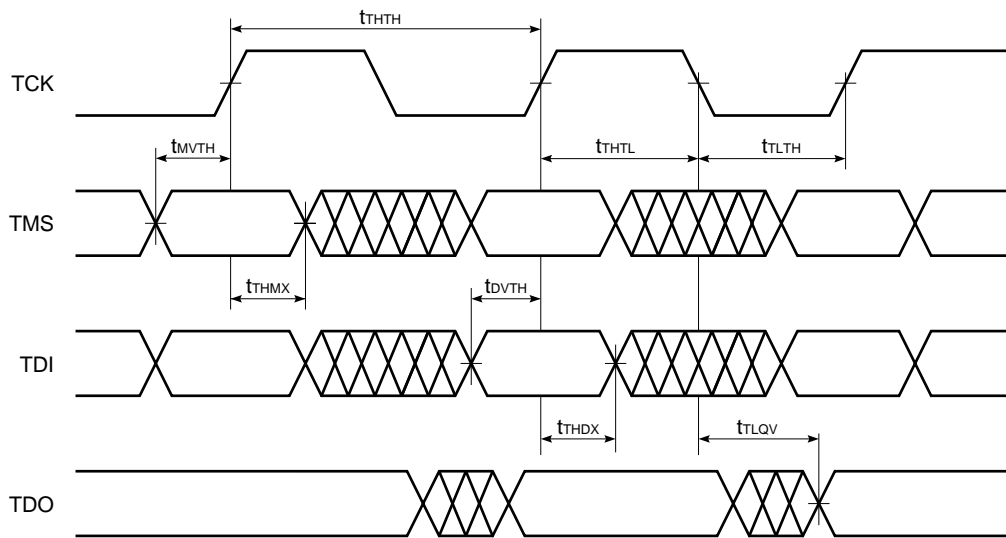
Output waveform



Output load ($V_{TT}=1.5$ V)



JTAG Timing Diagram



Scan Register Definition

Register name	256K x 18	128K x 36	Unit
Instruction register	3	3	bit
Bypass register	1	1	bit
ID register	32	32	bit
Boundary register	51	70	bit

ID Register Definition

Organization	ID [31:28] vendor revision no.	ID [27:12] part no.	ID [11:1] vendor ID no.	ID [0] fix bit
256K x 18	XXXX	0111001011 000000	00010010000	1
128K x 36	XXXX	0110101100 000000	00010010000	1

JTAG Instruction Cording

IR2	IR1	IR0	Instruction	Note
0	0	0	EXTEST	1
0	0	1	IDCODE	
0	1	0	SAMPLE-Z	1
0	1	1	BYPASS	
1	0	0	SAMPLE	
1	0	1	BYPASS	
1	1	0	BYPASS	
1	1	1	BYPASS	

Note 1. TRISTATE all data drivers and CAPTURE the pad values into a SERIAL SCAN LATCH.

SCAN Exit Order

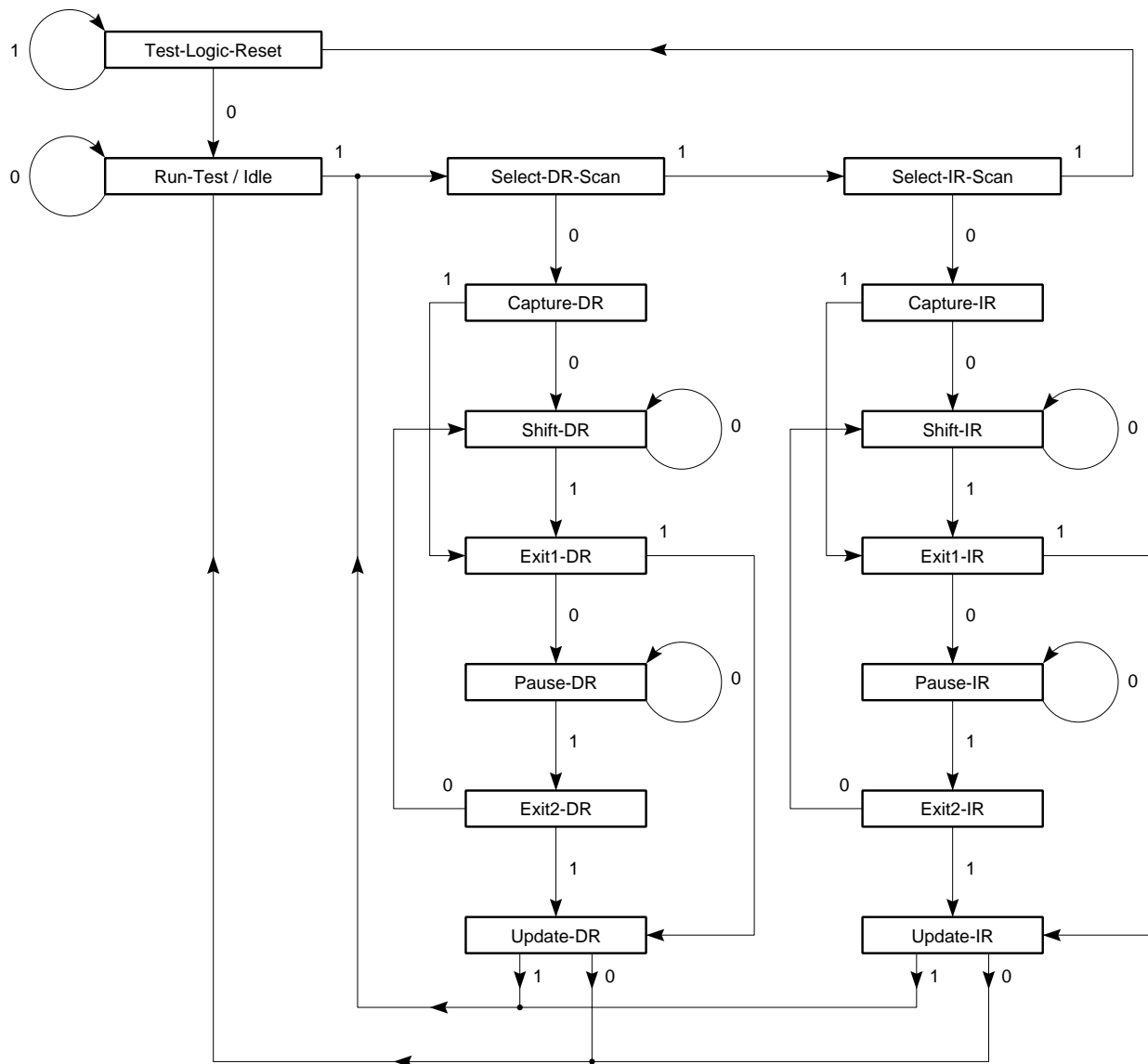
[μPD464318L (256K words by 18 bits)]

Bit no.	Signal name	Bump ID
1	M2	5R
2	SA5	6T
3	SA0	4P
4	SA4	6R
5	SA8	5T
6	NC	7T
7	DQa1	7P
8	DQa2	6N
9	DQa3	6L
10	DQa4	7K
11	/SBa	5L
12	/K	4L
13	K	4K
14	/G	4F
15	DQa5	6H
16	DQa6	7G
17	DQa7	6F
18	DQa8	7E
19	DQa9	6D
20	SA2	6A
21	SA3	6C
22	SA7	5C
23	SA6	5A
24	NC	6B
25	SA16	5B
26	SA17	3B
27	NC	2B
28	SA9	3A
29	SA10	3C
30	SA13	2C
31	SA12	2A
32	DQb1	1D
33	DQb2	2E
34	DQb3	2G
35	DQb4	1H
36	/SBb	3G
37	ZQ	4D
38	/SS	4E
39	NC	4G
40	NC	4H
41	/SW	4M
42	DQb5	2K
43	DQb6	1L
44	DQb7	2M
45	DQb8	1N
46	DQb9	2P
47	SA11	3T
48	SA14	2R
49	SA1	4N
50	SA15	2T
51	M1	3R

[μPD464336L (128K words by 36 bits)]

Bit no.	Signal name	Bump ID
1	M2	5R
2	SA0	4P
3	SA8	4T
4	SA4	6R
5	SA7	5T
6	NC	7T
7	DQa9	6P
8	DQa8	7P
9	DQa7	6N
10	DQa6	7N
11	DQa5	6M
12	DQa4	6L
13	DQa3	7L
14	DQa2	6K
15	DQa1	7K
16	/SBa	5L
17	/K	4L
18	K	4K
19	/G	4F
20	/SBb	5G
21	DQb1	7H
22	DQb2	6H
23	DQb3	7G
24	DQb4	6G
25	DQb5	6F
26	DQb6	7E
27	DQb7	6E
28	DQb8	7D
29	DQb9	6D
30	SA2	6A
31	SA3	6C
32	SA6	5C
33	SA5	5A
34	NC	6B
35	SA15	5B
36	SA16	3B
37	NC	2B
38	SA9	3A
39	SA10	3C
40	SA13	2C
41	SA12	2A
42	DQc9	2D
43	DQc8	1D
44	DQc7	2E
45	DQc6	1E
46	DQc5	2F
47	DQc4	2G
48	DQc3	1G
49	DQc2	2H
50	DQc1	1H
51	/SBc	3G
52	ZQ	4D
53	/SS	4E
54	/C	4G
55	C	4H
56	/SW	4M
57	/SBd	3L
58	DQd1	1K
59	DQd2	2K
60	DQd3	1L
61	DQd4	2L
62	DQd5	2M
63	DQd6	1N
64	DQd7	2N
65	DQd8	1P
66	DQd9	2P
67	SA11	3T
68	SA14	2R
69	SA1	4N
70	M1	3R

TAP Controller State Diagram



Disabling The Test Access Port

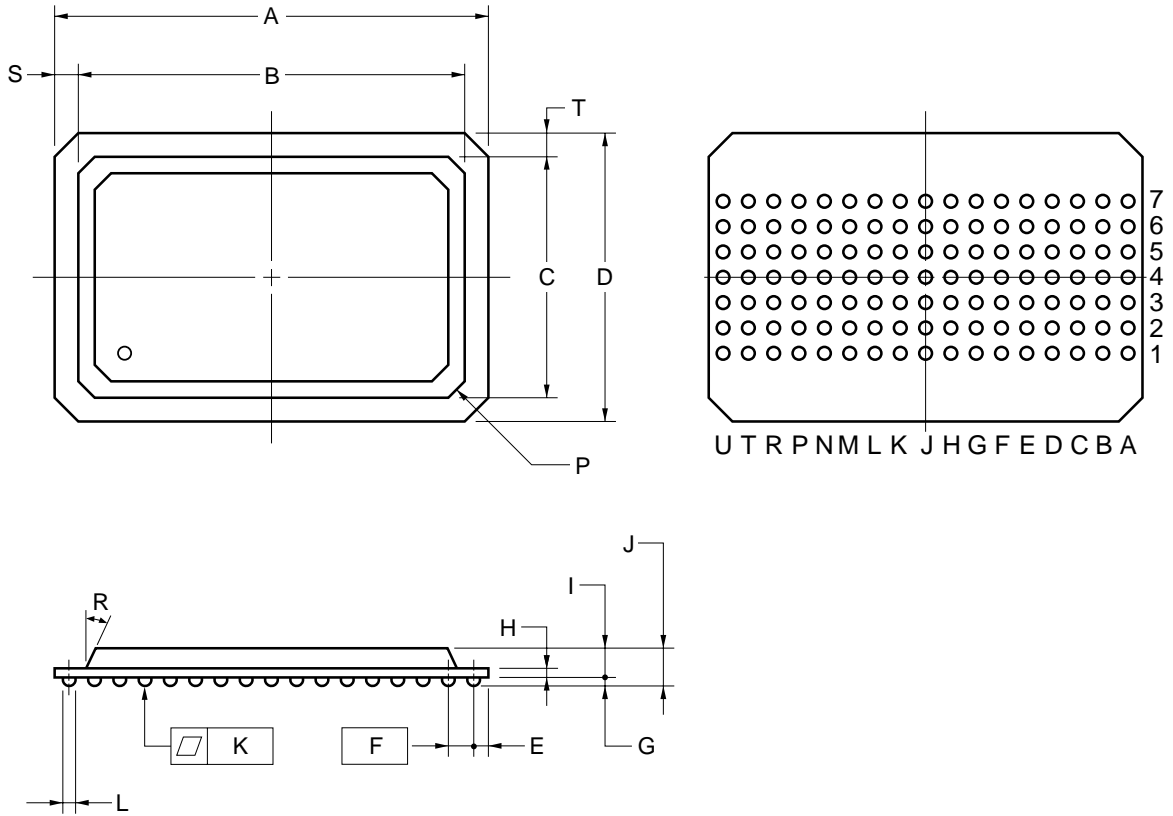
It is possible to use this device without utilizing the TAP. To disable the TAP Controller without interfering with normal operation of the device, TCK must be tied to Vss to preclude mid level inputs.

TDI and TMS are designed so an undriven input will produce a response identical to the application of a logic 1, and may be left unconnected. But they may also be tied to VDD through a 1 k resistor.

TDO should be left unconnected.

Package Drawing

119 PIN PLASTIC BGA



ITEM	MILLIMETERS	INCHES
A	22.0±0.2	0.866±0.008
B	19.5	0.768
C	12.0	0.472
D	14.0±0.2	0.551±0.008
E	0.84	0.033
F	1.27 (T.P.)	0.05 (T.P.)
G	0.6±0.1	0.024 ^{+0.004} _{-0.005}
H	0.56	0.022
I	1.46±0.1	0.057 ^{+0.005} _{-0.004}
J	2.30 MAX.	0.091
K	0.15	0.006
L	φ0.78±0.1	φ0.031 ^{+0.004} _{-0.005}
P	C0.7	C0.028
R	25°	25°
S	1.25	0.049
T	1.0	0.039

P119S1-R4

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD464318L and μ PD464336L.

Type of Surface Mount Device

μ PD464318LS1: 119-pin plastic BGA

μ PD464336LS1: 119-pin plastic BGA

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

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NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.